

Silicon NPN Power Transistors

2SC2810

DESCRIPTION

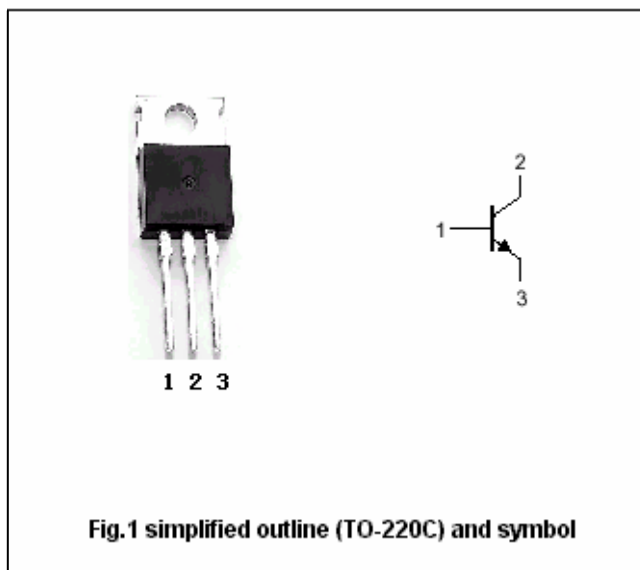
With TO-220C package
 ·High voltage,High speed

APPLICATIONS

·For power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7	A
I _{CM}	Collector current-peak		14	A
P _C	Collector dissipation	T _C =25℃	50	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A ; I _B =0.6A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A ; I _B =0.6A			1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =500V ; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			10	μA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	10			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		18		MHz

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PACKAGE OUTLINE

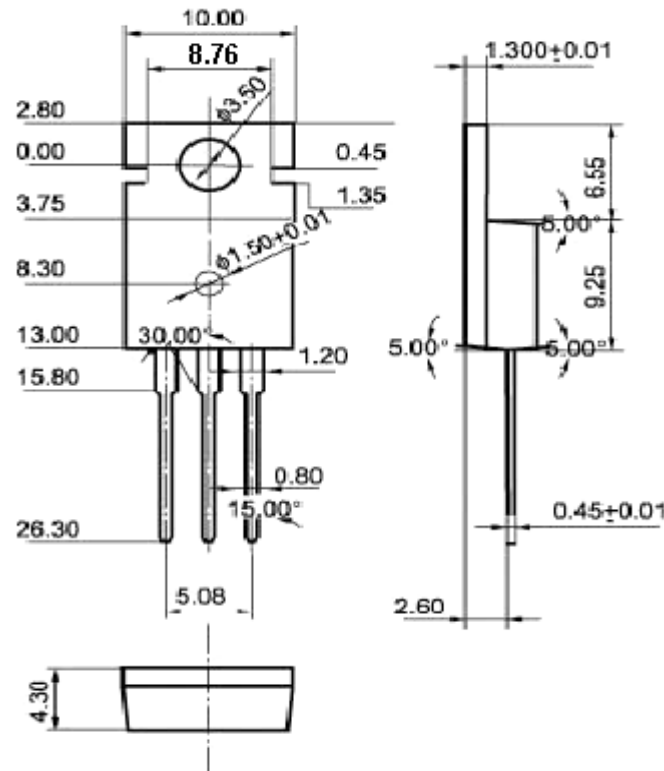


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)